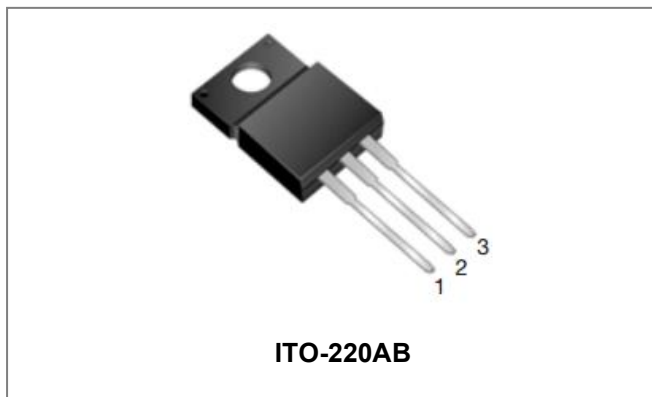


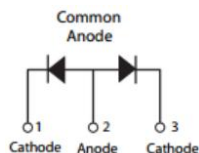
## MBRF2080CTR SCHOTTKY RECTIFIER



### Features

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Maximum Ratings(at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-	80	V
Working Peak Reverse Voltage	V <sub>RWM</sub>			
DC Blocking Voltage	V <sub>R</sub>			
Average Rectified Forward Current	I <sub>F(AV)</sub>	T <sub>c</sub> =116°C, In DC	10(Per Leg) 20(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	180	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Min.	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@10A, Pulse, T <sub>J</sub> = 25 °C	-	0.71	0.85	V
	V <sub>F2</sub>	@ 10A, Pulse, T <sub>J</sub> = 125 °C	-	0.63	0.75	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	-	0.07	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	-	25	150	mA
Junction Capacitance(Per Leg)	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C, f <sub>SIG</sub> = 1MHz	-	300	500	pF
Series Inductance(Per Leg)	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	-	10,000	V/μs
Isolation Voltage	V <sub>ISO</sub>	t = 1.0 second	3000	-	-	V
		t = 1.0 minute	2500	-	-	

\* Pulse width < 300 μs, duty cycle < 2%

## Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	°C
Storage Temperature	$T_{stg}$	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case(Per Leg)	$R_{\theta JC}$	DC operation	4	°C/W
Approximate Weight	wt	-	2	g

## Ratings and Characteristics Curves

Figure1 Typical Forward Characteristics

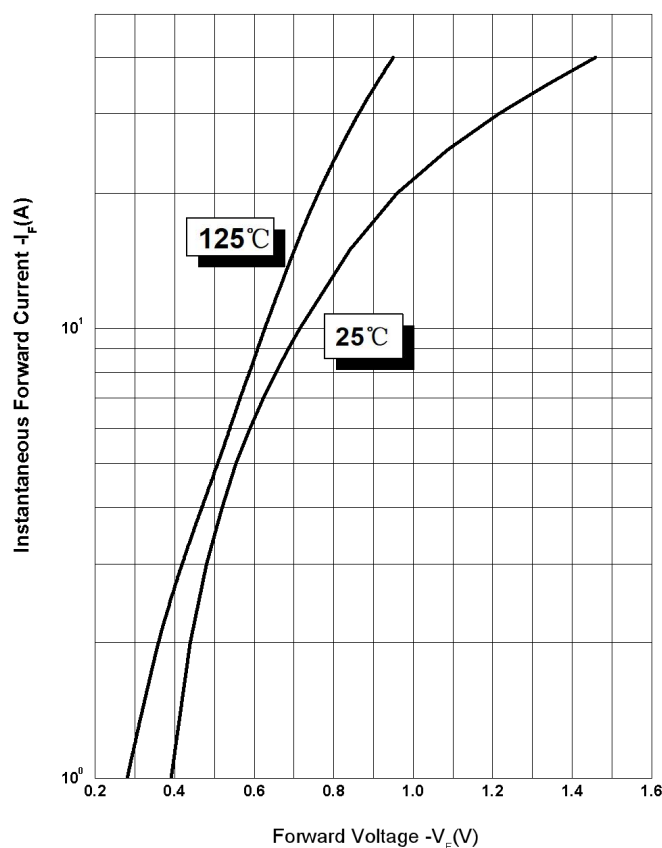


Figure 2 Typical Reverse Characteristics

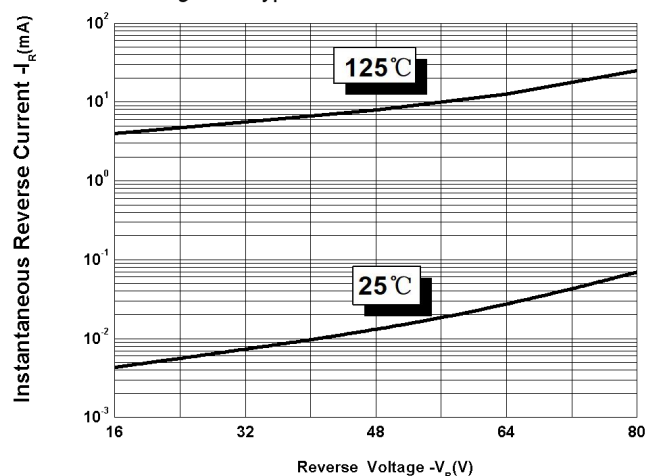
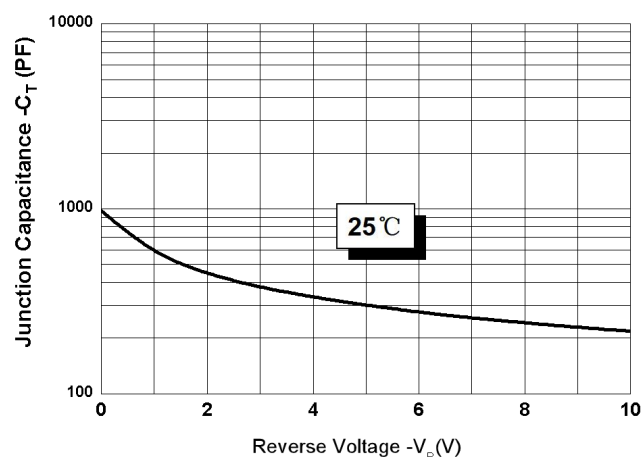
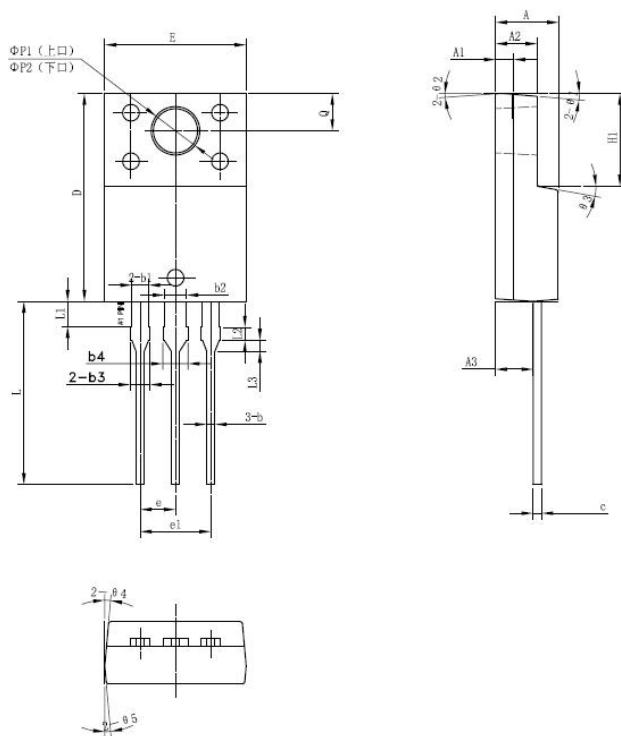


Figure 3 Typical Junction Capacitance

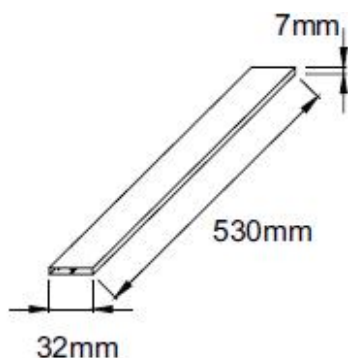


**Mechanical Dimensions ITO-220AB**

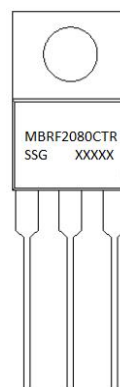


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

**Tube Specification**



**Marking Diagram**



Where XXXXX is YYWWL

MBR = Device Type  
 F = Package type  
 20 = Forward Current (20A)  
 80 = Reverse Voltage (80V)  
 CTR = Configuration  
 SSG = SSG  
 YY = Year  
 WW = Week  
 L = Lot Number

**Cautions:** Molding resin  
 Epoxy resin UL:94V-0

**Ordering Information**

Device	Package	Shipping
MBRF2080CTR	ITO-220AB (Pb-Free)	50 pcs/ tube

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